5-Line Transient Voltage Suppressor Array

This 5-line voltage transient suppressor array is designed for application requiring transient voltage protection capability. It is intended for use in over-transient voltage and ESD sensitive equipment such as computers, printers, automotive electronics, networking communication and other applications. This device features a monolithic common anode design which protects five independent lines in a single TSOP-6 package.

- Protects up to 5 Lines in a Single TSOP-6 Package
- Peak Power Dissipation 350 W (8 × 20 μs Waveform)
- ESD Rating of Class 3B (Exceeding 8.0 kV) per Human Body Model and Class C (Exceeding 400 V) per Machine Model
- Compliance with IEC 61000-4-2 (ESD) 15 kV (Air), 8.0 kV (Contact)
- Flammability Rating of UL 94 V-0
- These are Pb-Free Devices

Applications

- Hand-Held Portable Applications
- Networking and Telecom
- Automotive Electronics
- Serial and Parallel Ports
- Notebooks, Desktops, Servers

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

| Symbol | Rating | Value | Unit |
|-------------------|---|----------------------------------|------|
| P _{PK} 1 | Peak Power Dissipation 8 \times 20 μs Double Exponential Waveform (Note 1) | 350 | W |
| T_J | Operating Junction Temperature Range | -40 to 150 | °C |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| T_L | Lead Solder Temperature (10 s) | 260 | °C |
| ESD | Human Body Model (HBM) Machine Model (MM) IEC 61000-4-2 Air (ESD) IEC 61000-4-2 Contact (ESD) | >8000 >400 >15000 >8000 | V |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1

1. Non-repetitive current pulse per Figure 3.



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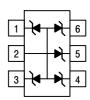
http://onsemi.com

TSOP-6 FIVE TRANSIENT VOLTAGE SUPPRESSOR 350 W PEAK POWER

PIN ASSIGNMENT



TSOP-6 **CASE 318G**



- PIN 1. CATHODE
 - 2. ANODE
 - 3. CATHODE
 - 4. CATHODE
 - 5. CATHODE
 - 6. CATHODE

MARKING DIAGRAM



- x = SMS05C:J
 - = SMS12C:K
 - = SMS15C:L
 - = SMS24C:M
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------|-----------|-----------------------|
| SMS05CT1G | | |
| SMS12CT1G | TSOP-6 | 3000/Tape & Reel |
| SMS15CT1G | (Pb-Free) | oooo, tape a ricer |
| SMS24CT1G | | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

$\textbf{SMS05C ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}\text{C unless otherwise specified})$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|----------------------------|-----------------|---|-----|-----|------|------|
| Reverse Working Voltage | V_{RWM} | (Note 2) | | | 5.0 | V |
| Breakdown Voltage | V_{BR} | I _T = 1.0 mA (Note 3) | 6.2 | | 7.2 | V |
| Reverse Leakage Current | I _R | V _{RWM} = 5.0 V | | | 5.0 | μΑ |
| Clamping Voltage | V _C | I_{PP} = 5.0 A (8 \times 20 μ s Waveform) | | | 9.8 | V |
| Clamping Voltage | V _C | I _{PP} = 24 A (8 × 20 μs Waveform) | | | 14.5 | V |
| Maximum Peak Pulse Current | I _{PP} | 8 × 20 μs Waveform | | | 24 | Α |
| Capacitance | CJ | V _R = 0 V, f = 1.0 MHz (Line to GND) | | 260 | 400 | pF |

SMS12C ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|----------------------------|-----------------|---|------|-------|-----|------|
| Reverse Working Voltage | V_{RWM} | (Note 2) | | | 12 | V |
| Breakdown Voltage | V_{BR} | I _T = 1.0 mA (Note 3) | 13.3 | | 15 | V |
| Reverse Leakage Current | I _R | V _{RWM} = 12 V | | 0.001 | 1.0 | μΑ |
| Clamping Voltage | V _C | I_{PP} = 5.0 A (8 \times 20 μ s Waveform) | | | 19 | V |
| Clamping Voltage | V _C | I _{PP} = 15 A (8 × 20 μs Waveform) | | | 23 | V |
| Maximum Peak Pulse Current | I _{PP} | 8 × 20 μs Waveform | | | 15 | Α |
| Capacitance | CJ | V _R = 0 V, f = 1.0 MHz (Line to GND) | | 120 | 150 | pF |

SMS15C ELECTRICAL CHARACTERISTICS ($T_J = 25$ °C, unless otherwise specified) (See Note 4)

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|----------------------------|------------------|---|-----|------|-----|------|
| Reverse Working Voltage | V _{RWM} | (Note 2) | | | 15 | V |
| Breakdown Voltage | V_{BR} | I _T = 1.0 mA (Note 3) | 17 | | 19 | V |
| Reverse Leakage Current | I _R | V _{RWM} = 15 V | | 0.05 | 1.0 | μΑ |
| Clamping Voltage | V _C | I_{PP} = 5.0 A (8 \times 20 μ s Waveform) | | | 24 | V |
| Clamping Voltage | V _C | I _{PP} = 12 A (8 × 20 μs Waveform) | | | 29 | V |
| Maximum Peak Pulse Current | I _{PP} | 8 × 20 μs Waveform | | | 12 | Α |
| Capacitance | CJ | V _R = 0 V, f = 1.0 MHz (Line to GND) | | 95 | 125 | pF |

$\textbf{SMS24C ELECTRICAL CHARACTERISTICS} \ (T_J = 25^{\circ}C, \ unless \ otherwise \ specified)$

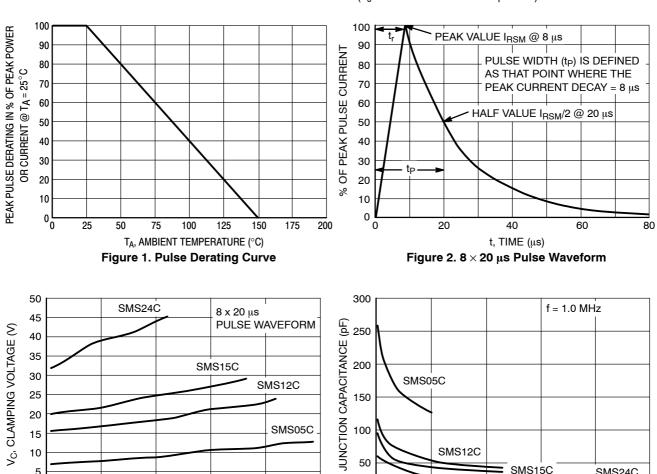
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|----------------------------|-----------------|---|------|-------|-----|------|
| Reverse Working Voltage | V_{RWM} | (Note 2) | | | 24 | V |
| Breakdown Voltage | V_{BR} | I _T = 1.0 mA (Note 3) | 26.7 | | 32 | V |
| Reverse Leakage Current | I _R | V _{RWM} = 24 V | | 0.001 | 1.0 | μΑ |
| Clamping Voltage | V _C | I _{PP} = 5.0 A (8 × 20 μs Waveform) | | | 40 | V |
| Clamping Voltage | V _C | I _{PP} = 8 A (8 × 20 μs Waveform) | | | 44 | V |
| Maximum Peak Pulse Current | I _{PP} | 8 × 20 μs Waveform | | | 8.0 | Α |
| Capacitance | CJ | V _R = 0 V, f = 1.0 MHz (Line to GND) | | 60 | 75 | pF |

^{2.} TVS devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.

3. V_{BR} is measured at pulse test current I_T.

4. Parametrics are the same for the Pb–Free packages, which are suffixed with a "G".

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise specified)



I_{PP}, PEAK PULSE CURRENT (A) Figure 3. Clamping Voltage vs. Peak Pulse Current

15

20

25

0

10

10

5

0

0

5

Figure 4. Junction Capacitance vs. Reverse Voltage

V_{BR}, REVERSE VOLTAGE (V)

10

SMS15C

15

SMS24C

25

20

SMS12C

5

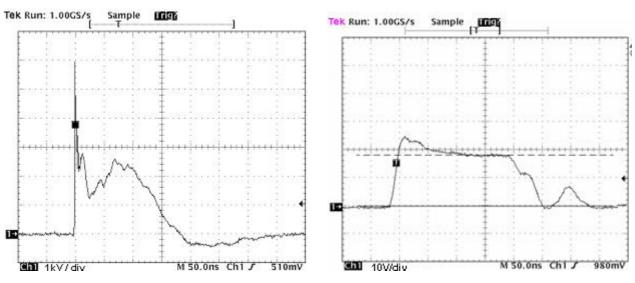


Figure 5. ESD Pulse IEC 61000-4-2 (8.0 kV Contact)

Figure 6. SMS15CT1 ESD Response for IEC 61000-4-2 (+8.0 kV Contact)

TYPICAL COMMON ANODE APPLICATIONS

A 5 TVS junction common anode design in a TSOP-6 package protects four separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. A simplified example of SMS05C Series Device applications is illustrated below.

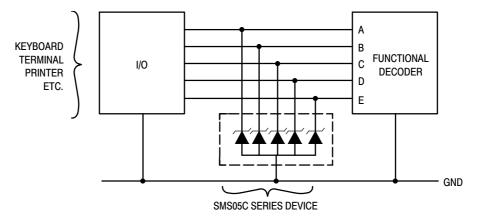


Figure 7. Computer Interface Protection

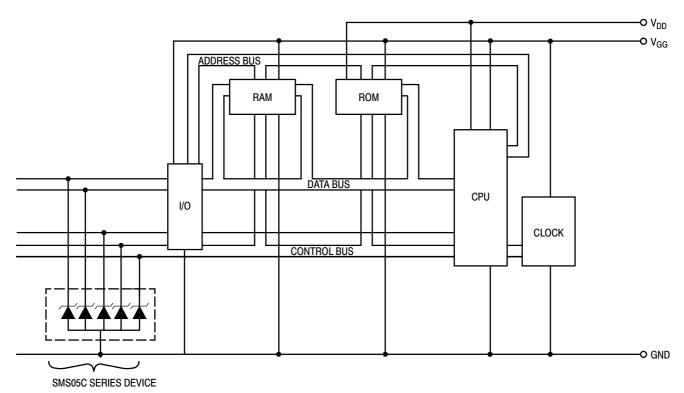
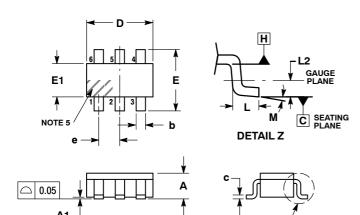


Figure 8. Microprocessor Protection

PACKAGE DIMENSIONS

TSOP-6 CASE 318G-02 **ISSUE U**



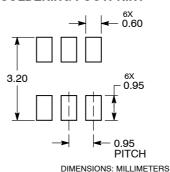
NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH.
- PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H
- 5. PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

| | MILLIMETERS | | | | | |
|-----|-------------|------|------|--|--|--|
| DIM | MIN | NOM | MAX | | | |
| Α | 0.90 | 1.00 | 1.10 | | | |
| A1 | 0.01 | 0.06 | 0.10 | | | |
| b | 0.25 | 0.38 | 0.50 | | | |
| С | 0.10 | 0.18 | 0.26 | | | |
| D | 2.90 | 3.00 | 3.10 | | | |
| E | 2.50 | 2.75 | 3.00 | | | |
| E1 | 1.30 | 1.50 | 1.70 | | | |
| е | 0.85 | 0.95 | 1.05 | | | |
| L | 0.20 | 0.40 | 0.60 | | | |
| L2 | 0.25 BSC | | | | | |
| М | 0° | _ | 10° | | | |

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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